Temperature dependence of pulse properties

in an n-type germanium detector

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Outline

- Introduction: germanium detectors
- Experimental setup
- Theoretical model
- Event selection
- Extraction of the rise time
- Summary



Summary

Introduction

Semiconductors detectors are used to register radiation:



Requirements for GeDes:

- cooled down ($T \sim 77$ K) to reduce thermal excitation.
- high voltage (few kV) applied to reduce the number of free charge carriers



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Semiconductors detectors are used to register radiation:



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- cooled down ($T \sim 77$ K) to reduce thermal excitation.
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Created electrons and holes drift \rightarrow induced signal is collected



Rise time extraction

Summary

Detector Siegfried-II



- Segmented 18-fold $(3z \times 6\phi)$;
- High-purity detector (electrically active impurities concentration $0.35 0.55 \cdot 10^{10}/\text{cm}^3$);
- Operation voltage 2000+ V.



Rise time extraction

Summary



Introduction: germanium detectors

- Experimental setup
 - Test stands
 - Temperature monitoring
- Theoretical model
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(Experimental setup)

Theoretical model

Event selection

Rise time extraction

Summary

Test stands @ MPI

Two test stands were used:





Gerdalinchen II, detectors submerged in LN2 at fixed T = 77.4 K; K1 detector in vacuum cooled through a cooling finger at varying T = 90-120 K.



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Collected datasets

Orientation	DS1@77 K	DS2@95–100 K	DS3@100-120 K
Along $\langle 110 \rangle$ axis	0°	0°	5°
Along $\langle 100 \rangle$ axis		45°	50°



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Summary

Collected datasets

Orientation	DS1@77 K	DS2@95–100 K	DS3@100-120 K
Along $\langle 110 \rangle$ axis	0°	0°	5°
Along $\langle 100 \rangle$ axis		45°	50°
$\langle 110 angle + 5^{\circ}$	5°		5°
$\langle 110 angle$ - 15°	-15°		-15°



Temperature monitoring in K1



DS2: One set of T measurements during data taking DS3: Two sets of T measurements before and after data taking



Rise time extraction

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(Theoretical model)

Event selection

Theoretical model

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Electrical field in a true-coax detector:

Poisson equation:
$$\Delta \phi(\mathbf{x}) = -\frac{1}{\epsilon_0 \epsilon} \rho(\mathbf{x}) \Rightarrow$$

 $E(r) = |\mathbf{E}(r)| = \frac{e\rho}{2\epsilon_0 \epsilon} r + \frac{V - (e\rho/4\epsilon_0 \epsilon)(r_2^2 - r_1^2)}{r \ln(r_2/r_1)}$

$$\begin{split} & \mu_{e/h}^{\text{eff}} \text{ - approximation for} \\ & \approx \text{homogeneous EF;} \\ & \mu_e^T \text{ - } T\text{-independent constant} \end{split}$$

Velocity:
$$v_{e/h} = \mu_{e/h}^{\text{eff}} E(r)$$

Theory*: $\mu_e^{\text{eff}} = \mu_e^T \cdot T^{-3/2}$

$$\begin{split} \mathbf{v} &= d\mathbf{r}/dt = \mu_e^T \cdot T^{-3/2} \cdot \left(A\mathbf{r} + \frac{B}{r}\right) \Rightarrow \\ |\text{solve}| &\Rightarrow \text{For drift from the outside in:} \\ t(\mathbf{r}) &= \frac{\ln\left(\frac{Ar_2^2 + B}{Ar^2 + B}\right)}{2A} \cdot \frac{T^{3/2}}{\mu_e^T}; \\ \text{Rise time:} \ t_{\text{rise}} &= C \cdot \frac{T^{3/2}}{\mu_e^T}. \end{split}$$

For Siegfried-II:

$$r_1 = 5 \text{ mm}$$

 $r_2 = 37.5 \text{ mm}$
 $\rho = 0.45 \cdot 10^{10} / \text{cm}^3$
 $V = 2000 \text{ V}$

* Phys. Rev. **80** (1950) 72, based on scattering off phonons



Summary



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Event selection

- Only events induced by 122 $keV \pm 2\sigma$ photons from ¹⁵²Eu;
- Single segment event (only one segment above $E_{\text{threshold}} = 20 \text{ keV}$).





(Rise time extraction

Summary



- Introduction: germanium detectors
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- Extraction of the rise time
 - Pulse properties: amplitude, rise time
 - Fit with simulated pulses

• Summary



Summary





*DAQ had 75 MHz sampling frequency



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Temperature dependence of pulse properties

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(Rise time extraction)

Summary

Pulse properties: amplitude





Summary

Pulse properties: rise time





Event selection

Pulse fitting

Pulse example with the fit of simulated pulse:



Simulated pulse*:

- 1 GHz sampling frequency
- Single hit at depth 5 mm and $\phi = 0^{\circ} \rightarrow {\rm axis} < 110 >$

Three parameters of the fit, one of which is $t_{\rm scale} \propto \frac{1}{t_{\rm rise}}.$

^kEur. Phys. J. C (2010) **68** 609



Event selection

ection (Rise

(Rise time extraction)

Summary

Pulse fitting

Pulse example with the fit of simulated pulse:



Only good fits were considered



Theoretical model

Event selection

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(Rise time extraction)

Summary

Temperature dependence of pulse lengths: results





Temperature dependence of pulse lengths: results

Slow axis $\langle 110
angle$ becomes faster than the fast axis $\langle 100
angle$ at ~ 107 K?



Possible explanation:

• measurements of two germanium samples* showed conductivity change with temperature: electrical field is temperature dependent?



IKZ, K. Irmscher, private communication

Summary

Summary and conclusions

- Measurements do not agree with the simple model predictions (theoretical $T^{3/2}$, experimental $T^{1.66}$ and $T^{1.6}$);
- Boltzmann-like ansatz works fine;
- The old measurements of mobilities* are precise, therefore some detector-specific effects affect the results;
- Note: pulse amplitudes were stable for T range 95–120 K \rightarrow the detector can be stably operated well above 100 K.

*Nucl. Instrum. Meth. A 569, 764(2006)



Thank you for your attention!









Simulated pulse



Segment pulse

Core pulse

Simulated pulse

Properties:

- single hit at depth 5 mm and $\phi = 0^{\circ} \rightarrow$ axis <110>;
- impurity level $0.45 \cdot 10^{10} / \text{cm}^3$;
- electron mobility constant 38609 (38536) mm²/Vs for $\langle 100\rangle$ ($\langle 111\rangle)$ axis;
- grid for numerical calculation $32(r) \times 180(\phi) \times 70(z)$;
- 1 GHz sampling frequency, corresponding to 1 ns step;
- bandwidth of pprox 10 MHz;
- amplifier decay time 50 μ s;
- o no noise.



Temperature dependence of pulse lengths: Core





Temperature dependence of pulse lengths: Segment



